

128 K × 8 Ultimate CMOS SRAM

Introduction

The M 65608 is a very low power CMOS static RAM organized as 131072 × 8 bits. It is manufactured using the MHS high performance CMOS technology named SCMOS.

With this process, MHS brings the solution to applications where fast computing is as mandatory as low consumption, such as aerospace electronics, portable instruments, or embarked systems.

Utilizing an array of six transistors (6T) memory cells, the

M 65608 combines an extremely low standby supply current (Typical value = 0.2 μA) with a fast access time at 25 ns over the full commercial temperature range. The high stability of the 6T cell provides excellent protection against soft errors due to noise.

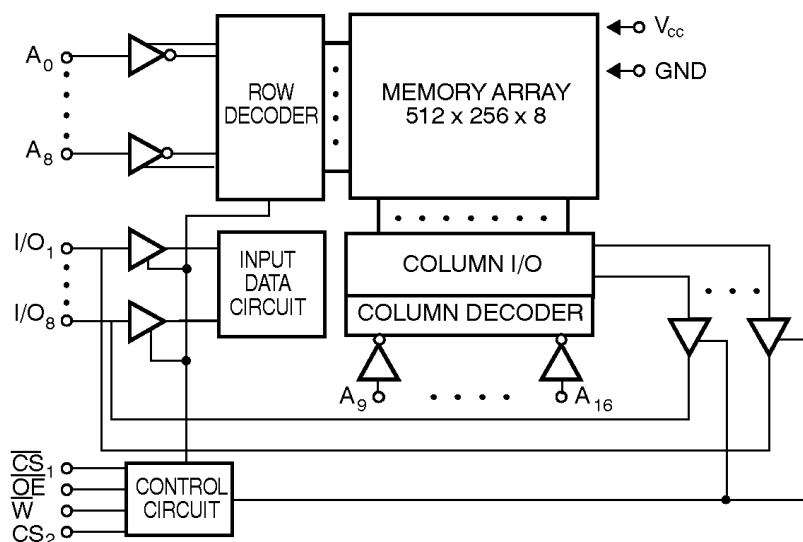
For military/space applications that demand superior levels of performance and reliability the M 65608 is processed according to the methods of the latest revision of the MIL STD 883 (class B or S) and/or ESA SCC 9000.

Features

- Access time : commercial : 25/30/35/45 ns
industrial and military : 25(*)/30/35/45 ns
 - Very low power consumption
active : 250 mW (Typ)
standby : 1 μW (Typ)
data retention : 0.5 μW (Typ)
 - Wide temperature Range : -55 To +125°C
 - 400 Mils width package
 - TTL compatible inputs and outputs
 - Asynchronous
 - Single 5 volt supply
 - Equal cycle and access time
 - Gated inputs :
no pull-up/down
resistors are required
- (*) Preview

Interface

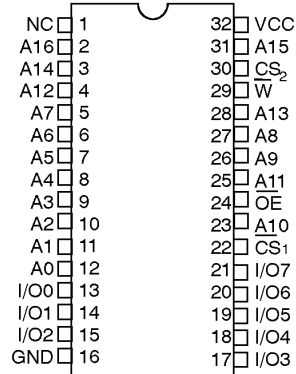
Block Diagram



M 65608

Pin Configuration

32 pins DLCC ceramic 400 MILS
 32 pins DIL side-brazed 400 MILS
 32 pins Flatpack 400 MILS
 32 pins PDIL 400 MILS
 32 pins SOIC and SOJ 400 MILS



Pin Names

A0–A16	Address inputs
I/O0–I/O7	Data Input/Output
\overline{CS}_1	Chip select 1
CS_2	Chip select 2
\overline{W}	Write Enable
\overline{OE}	Output Enable
VCC	Power
GND	Ground

Truth Table

\overline{CS}_1	CS_2	\overline{W}	\overline{OE}	INPUTS/ OUTPUTS	MODE
H	X	X	X	Z	Deselect/ Power-down
X	L	X	X	Z	Deselect/ Power Down
L	H	H	L	Data Out	Read
L	H	L	X	Data In	Write
L	H	H	H	Z	Output Disable

L = low, H = high, X = H or L, Z = high impedance.

Electrical Characteristics

Absolute Maximum Ratings

Supply voltage to GND potential : - 0.5 V + 7.0 V Storage temperature : -65 °C to + 150 °C
 DC input voltage : GND - 0,3 V to VCC + 0,3 Output current into outputs (low) : 20 mA
 DC output voltage high Z state : GND - 0,3 V to VCC + 0,3 Electro statics discharge voltage : > 2 001 V
 (MIL STD 883D method 3015.3)

Operating Range

	OPERATING VOLTAGE	OPERATING TEMPERATURE
Military	5 V ± 10 %	- 55 °C to + 125 °C
Industrial	5 V ± 10 %	- 40 °C to + 85 °C
Commercial	5 V ± 10 %	0 °C to + 70 °C

Recommended DC Operating Conditions

PARAMETER	DESCRIPTION	MINIMUM	TYPICAL	MAXIMUM	UNIT
Vcc	Supply voltage	4.5	5.0	5.5	V
Gnd	Ground	0.0	0.0	0.0	V
VIL	Input low voltage	GND - 0.3	0.0	0.8	V
VIH	Input high voltage	2.2	-	V _{CC} + 0.3	V

Capacitance

PARAMETER	DESCRIPTION	MINIMUM	TYPICAL	MAXIMUM	UNIT
Cin (1)	Input low voltage	-	-	8	pF
Cout (1)	Output high volt	-	-	8	pF

Note : 1. Guaranteed but not tested.

DC Parameters

PARAMETER	DESCRIPTION	MINIMUM	TYPICAL	MAXIMUM	UNIT
IIX (2)	Input leakage current	- 1	-	1	µA
IOZ (2)	Output leakage current	- 1	-	1	µA
VOL (3)	Output low voltage	-	-	0.4	V
VOH (4)	Output high voltage	2.4	-	-	

Notes : 2. Gnd < Vin < Vcc, Gnd < Vout < Vcc Output Disabled.
 3. Vcc min. IOL = 8.0 mA.
 4. Vcc min. IOH = -4.0 mA.

Consumption for Commercial

SYMBOL	DESCRIPTION	65608L/V – 25	65608L/V – 30	65608L/V – 35	65608L/V – 45	UNIT	VALUE
ICCSB (5)	Standby supply current	5/2	5/2	5/2	5/2	mA	max
ICCSB ₁ (6)	Standby supply current	500/50	500/50	500/50	500/50	μA	max
ICCOP (7)	Dynamic operating current	150	140	130	120	mA	max

Consumption for Industrial

SYMBOL	DESCRIPTION	65608L/V (*) – 25	65608L/V – 30	65608L/V – 35	65608L/V – 45	UNIT	VALUE
ICCSB (5)	Standby supply current	5/2	5/2	5/2	5/2	mA	max
ICCSB ₁ (6)	Standby supply current	700/100	700/100	700/100	700/100	μA	max
ICCOP (7)	Dynamic operating current	160	150	140	120	mA	max

Consumption for Military

SYMBOL	DESCRIPTION	65608L/V (*) – 25	65608L/V – 30	65608L/V – 35	65608L/V – 45	UNIT	VALUE
ICCSB (5)	Standby supply current	5/2.5	5/2.5	5/2.5	5/2.5	mA	max
ICCSB ₁ (6)	Standby supply current	1 000/300	1 000/300	1 000/300	1 000/300	μA	max
ICCOP (7)	Dynamic operating current	160	150	140	120	mA	max

- Notes :
- $\overline{CS}_1 \geq V_{IH}$ or $CS_2 \leq V_{IL}$ and $\overline{CS}_1 \leq V_{IL}$.
 - $\overline{CS}_1 \geq V_{cc} - 0.3 V$ or, $CS_2 < Gnd + 0.3 V$ and $\overline{CS}_1 \leq 0.2 V$
 - $F = 1/TAVAV$, $I_{out} = 0 mA$, $\overline{W} = \overline{OE} = V_{IH}$, $V_{in} = Gnd/V_{cc}$, V_{cc} max.
- (*) preview.

AC Parameters

Input pulse levels : Gnd to 3.0 V Input timing reference levels : 1.5 V
 Input rise : 5 ns Output loading IOL/IOH (see figure 1a and 1b) : + 30 pF

AC Test Loads Waveforms

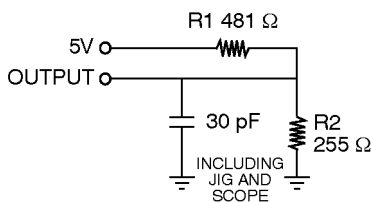


Figure 1a

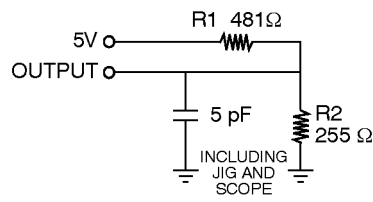


Figure 1b

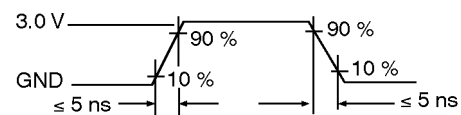
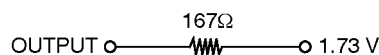


Figure 2

Equivalent to : THEVENIN EQUIVALENT

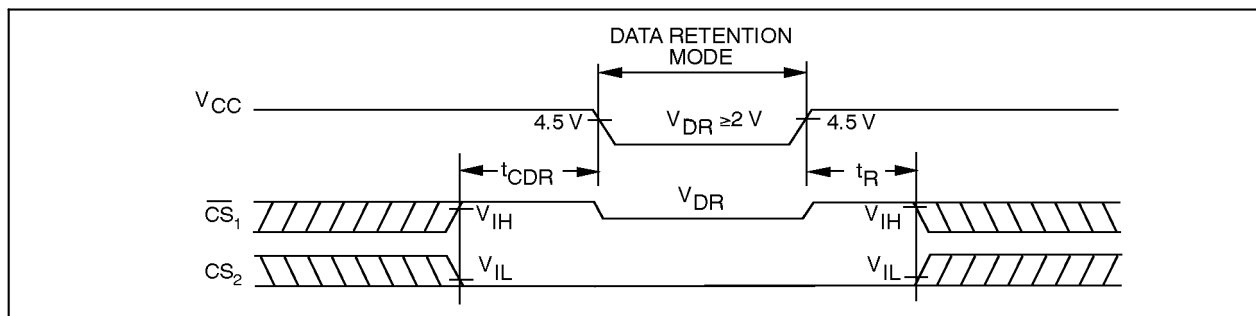


Data Retention Mode

MHS CMOS RAM's are designed with battery backup in mind. Data retention voltage and supply current are guaranteed over temperature. The following rules insure data retention :

- During data retention chip select \overline{CS}_1 must be held high within V_{CC} to $V_{CC} - 0.2$ V or, chip select CS_2 must be held low within GND to $GND + 0.2$ V.
- Output Enable (\overline{OE}) should be held high to keep the RAM outputs high impedance, minimizing power dissipation.
- During power up and power down transitions \overline{CS}_1 and \overline{OE} must be kept between $V_{CC} + 0.3$ V and 70 % of V_{CC} , or with CS_2 between GND and $GND - 0.3$ V.
- The RAM can begin operation > 45 ns after V_{cc} reaches the minimum operation voltages (4.5 V).

Timing



Data Retention Characteristics

PARAMETER	DESCRIPTION	MINIMUM	TYPICAL $T_A = 25^\circ C$	MAXIMUM			UNIT
VCCDR	Vcc for data retention	2.0	-	-			V
TCDR	Chip deselect to data retention time	0.0	-	-			ns
TR	Operation recovery time	TAVAV (9)	-	-			ns
ICCDR1 (10)	Data retention current @ 2.0 V : M-65608-V M-65608-L	-	0.1	COM 20	IND 40	MIL 150	μA
		-	0.1	200	300	500	μA
ICCDR2 (10)	Data retention current @ 3.0 V : M-65608-V M-65608-L	-	0.2	COM 30	IND 60	MIL 200	μA
		-	0.2	300	450	600	μA

Notes : 9. TAVAV = Read cycle time.

10. $\overline{CS}_1 = V_{cc}$ or $CS_2 = \overline{CS}_1 = GND$, $V_{in} = Gnd/V_{cc}$, this parameter is only tested at $V_{cc} = 2$ V.

Write Cycle

SYMBOL	PARAMETER	65608L/V (*) – 25	65608L/V – 30	65608L/V – 35	65608L/V – 45	UNIT	VALUE
TAVAV	Write cycle time	25	30	35	45	ns	min
TAVWL	Address set-up time	0	0	0	0	ns	min
TAVWH	Address valid to end of write	20	22	25	35	ns	min
TDVWH	Data set-up time	15	18	20	25	ns	min
TE ₁ LWH	\overline{CS}_1 low to write end	20	22	25	35	ns	min
TE ₂ HWH	CS ₂ high to write end	20	22	25	35	ns	min
TWLQZ	Write low to high Z (11)	8	8	10	15	ns	max
TWLWH	Write pulse width	20	22	25	35	ns	min
TWHAX	Address hold from to end of write	0	0	0	0	ns	min
TWHDX	Data hold time	0	0	0	0	ns	min
TWHQX	Write high to low Z (11)	0	0	0	0	ns	min

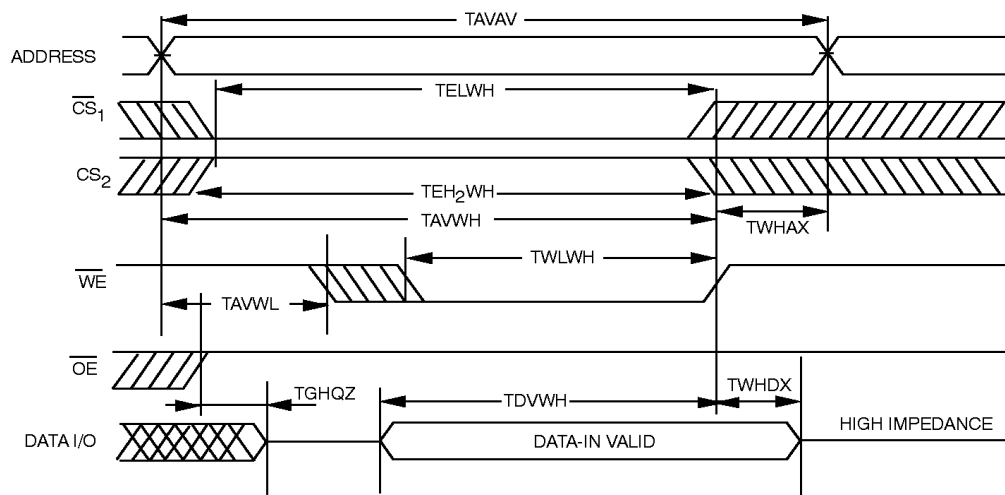
Read Cycle

SYMBOL	PARAMETER	65608L/V (*) – 25	65608L/V – 30	65608L/V – 35	65608L/V – 45	UNIT	VALUE
TAVAV	Read cycle time	25	30	35	45	ns	min
TAVQV	Address access time	25	30	35	45	ns	max
TAVQX	Address valid to low Z	3	5	5	5	ns	min
TE ₁ LQV	Chip-select ₁ access time	25	30	35	45	ns	max
TE ₁ LQX	\overline{CS}_1 low to low Z (11)	3	3	3	3	ns	min
TE ₁ HQZ	\overline{CS}_1 high to high Z (11)	15	18	20	20	ns	max
TE ₂ HQV	Chip-select ₂ access time	25	30	35	45	ns	max
TE ₂ HQX	CS ₂ high to low Z (11)	3	3	3	3	ns	min
TE ₂ LQZ	CS ₂ low to high Z (11)	15	18	20	20	ns	max
TGLQV	Output Enable access time	10	12	12	15	ns	max
TGLQX	\overline{OE} low to low Z (11)	0	0	0	0	ns	min
TGHQZ	\overline{OE} high to high Z (11)	8	8	10	15	ns	max

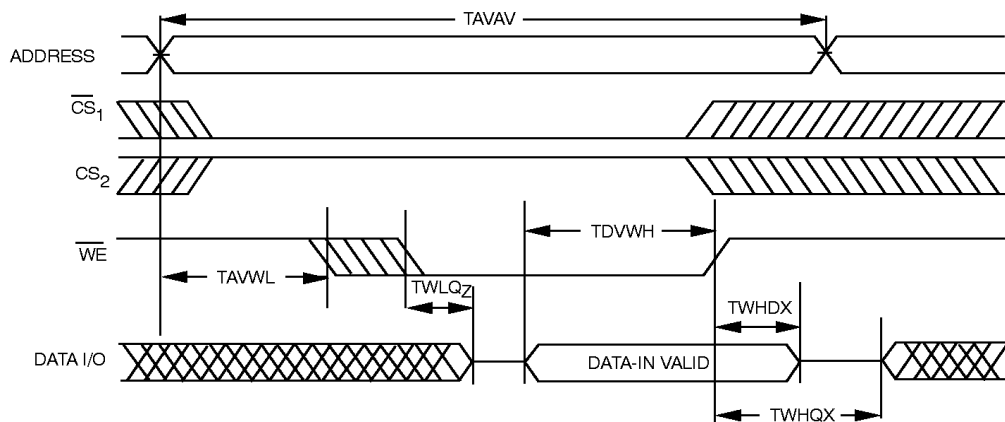
Notes : 11. Parameters guaranteed, not tested, with output loading 5 pF. (see fig. 1.b.).

(*) Preview for industrial and military.

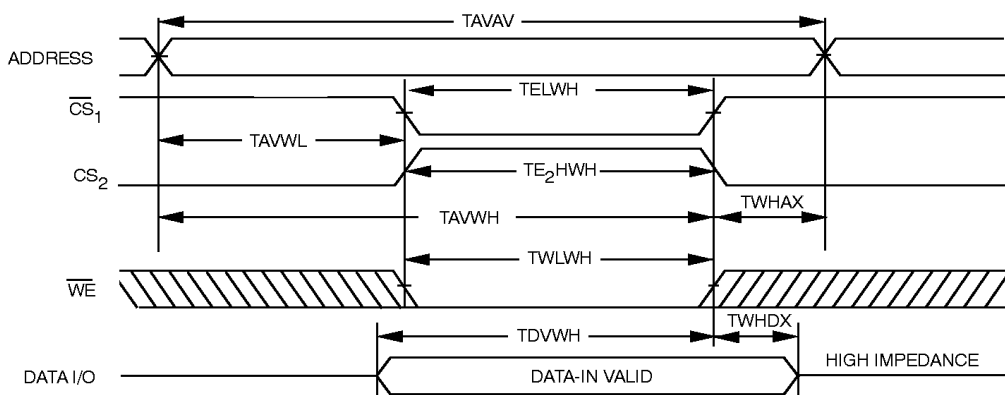
Write Cycle 1. \overline{W} Controlled. \overline{OE} High During Write



Write Cycle 2. \overline{W} Controlled. \overline{OE} Low



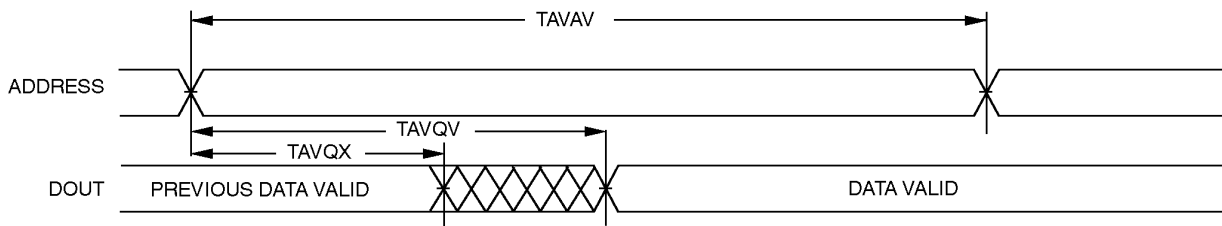
Write Cycle 3. \overline{CS}_1 or \overline{CS}_2 Controlled.



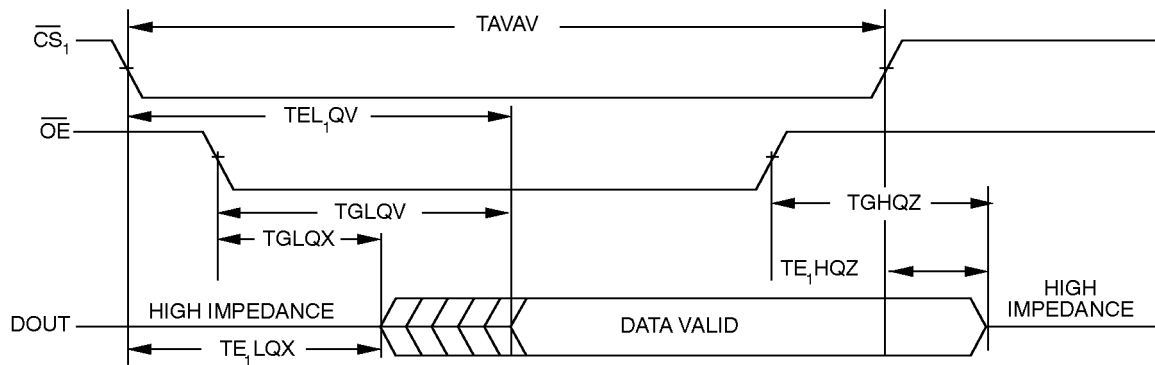
Note : 12. The internal write time of the memory is defined by the overlap of \overline{CS}_1 Low and CS₂ HIGH and \overline{W} LOW. Both signals must be activated to initiate a write and either signal can terminate a write by going in activated. The data input setup and hold timing should be referenced to the activated edge of the signal that terminates the write. Data out is high impedance if $\overline{OE} = V_{IH}$.

M 65608

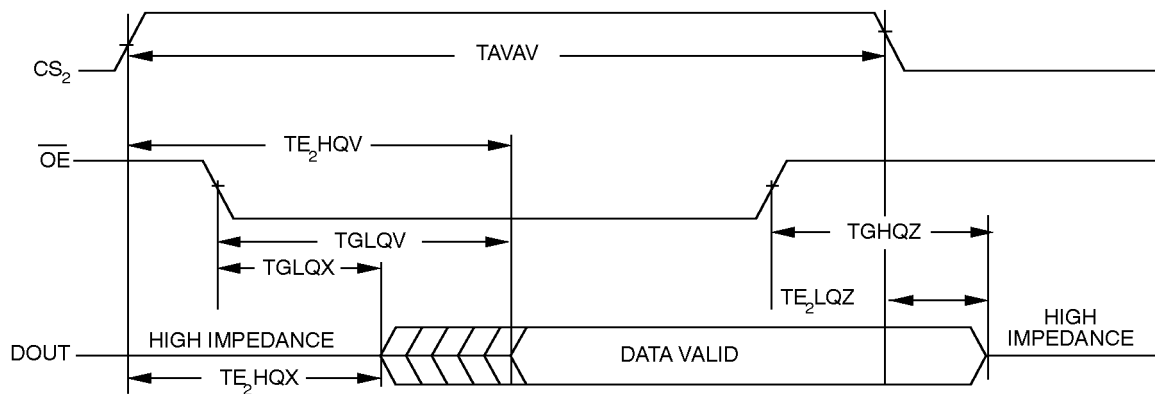
Read Cycle nb 1



Read Cycle nb 2



Read Cycle nb 3



Ordering Information

TEMPERATURE RANGE	PACKAGE	DEVICE	GRADE	SPEED	FLOW	
M	M	CJ	- 65608	EV	- 45	/883
C = Commercial I = Industrial M = Military S = Space	0° to +70°C -40° to +85°C -55° to +125°C -55° to +125°C CJ = Side Brazed 32 pins 400 mils D1 = Flat Package 32 pins 400 mils 4J = Dual LCC 32 pins 39 = Plastic DIL 32 pins 400 mils T1 = 32 pins SOIC 400 mils U1 = 32 pins SOJ 400 mils	128K × 8 STATIC RAM : R = Tape & Reel : RD = Tape & Reel and Dry pack : D = Dry pack	L = Low power V = Very low power EL = Low power and rad tolerant EV = Very low power and rad tolerant	25 ns 30 ns 35 ns 45 ns	blank = MHS standards /883 = MIL-STD 883 Class B or S CB = Compliant CECC 90000 Level B SHXXX = Special customer request FHXXX = Flight models (space) MHXXX = Mechanical parts (space) LHXXX = Life test parts (space)	

The information contained herein is subject to change without notice. No responsibility is assumed by MATRA MHS SA for using this publication and/or circuits described herein : nor for any possible infringements of patents or other rights of third parties which may result from its use.